# **Small Signal MOSFET**

# 20 V, 540 mA, Dual N-Channel

# Features

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

# **Applications**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

# **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted.)

Paramet	Symbol	Value	Unit		
Drain-to-Source Voltage			V <sub>DSS</sub>	20	V
Gate-to-Source Voltage			$V_{GS}$	±7.0	V
Continuous Drain Current	Steauv A			540	mA
(Note 1)	State	$T_A = 85^{\circ}C$	I <sub>D</sub>	390	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	250	mW
Continuous Drain Current	t ≤ 5 s	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$	I_	570	mA
(Note 1)	1 = 33	$T_A = 85^{\circ}C$	I <sub>D</sub>	410	
Power Dissipation (Note 1)	t:	≤ 5 s	P <sub>D</sub>	280	mW
Pulsed Drain Current	Ised Drain Current $t_p = 10 \mu s$			1.5	Α
Operating Junction and Stor	T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C		
Source Current (Body Diode)			IS	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{ heta JA}$	500	°C/W
Junction–to–Ambient – $t \le 5$ s (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

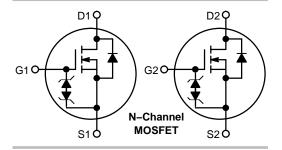
 Surface mounted on FR4 board using 1 in sq pad size (Cu. area = 1.127 in sq [1 oz] including traces).



# ON Semiconductor®

## www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ	I <sub>D</sub> Max (Note 1)	
20	400 mΩ @ 4.5 V		
	500 mΩ @ 2.5 V	540 mA	
	700 mΩ @ 1.8 V		







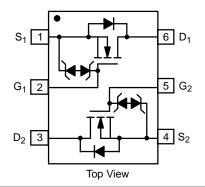
**MARKING** 

TV = Specific Device Code

M = Date Code ■ Pb–Free Package

(Note: Microdot may be in either location)

## PINOUT: SOT-563



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25$ °C unless otherwise noted.)

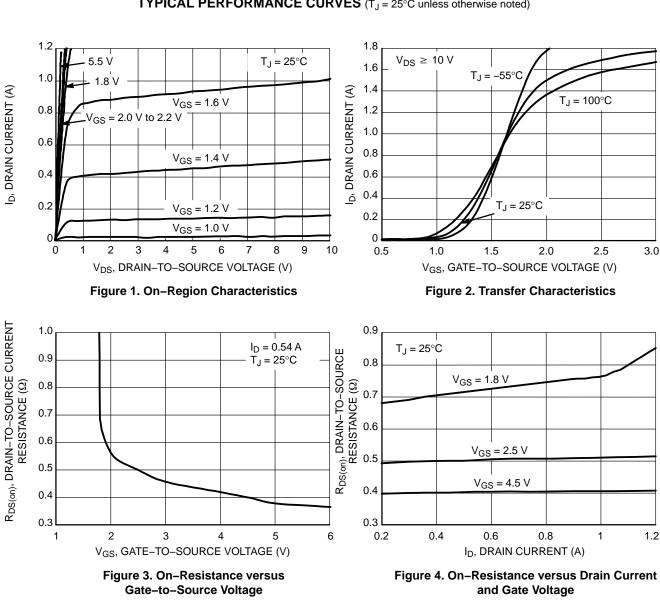
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	_	_	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	-		-	14	-	mV/°C
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	T <sub>J</sub> = 25°C	_	-	1.0	μΑ
	I <sub>DSS</sub>	V <sub>DS</sub> = 16 V	T <sub>J</sub> = 125°C	-	-	5.0	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4$	1.5 V	-	_	±5.0	μΑ
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 250$	) μΑ	0.45	_	1.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	-		-	2.0	_	mV/°C
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 540$	) mA	-	0.4	0.55	Ω
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 500 \text{ mA}$		-	0.5	0.7	1
		$V_{GS} = 1.8 \text{ V}, I_D = 350$	) mA	-	0.7	0.9	
Forward Transconductance	9FS	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 540 mA			1.0	_	S
CHARGES AND CAPACITANCES	•						
Input Capacitance	C <sub>ISS</sub>			_	80	150	pF
Output Capacitance	C <sub>OSS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 16 V			13	25	1
Reverse Transfer Capacitance	C <sub>RSS</sub>				10	20	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V; I <sub>D</sub> = 540 mA		_	1.5	2.5	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			_	0.1	_	
Gate-to-Source Charge	Q <sub>GS</sub>			_	0.2	_	
Gate-to-Drain Charge	$Q_{GD}$	1			0.35	_	
SWITCHING CHARACTERISTICS, V <sub>GS</sub> = V (	Note 4)						
Turn-On Delay Time	t <sub>d(ON)</sub>			_	6.0	_	ns
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 540 mA, $R_{G}$ = 10 $\Omega$		_	4.0	_	1
Turn-Off Delay Time	t <sub>d(OFF)</sub>			_	16	_	
Fall Time	t <sub>f</sub>	1			8.0	_	
DRAIN-SOURCE DIODE CHARACTERISTIC	s						
Forward Diode Voltage		Vcs = 0 V	T <sub>J</sub> = 25°C	_	0.7	1.2	V
	$V_{SD}$	$V_{GS} = 0 \text{ V},$ $I_S = 350 \text{ mA}$		_	0.6	_	
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V}, d_{ISD}/d_t = 100 \text{ A/}\mu\text{s}, I_S = 350 \text{ mA}$		-	6.5	_	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surface—mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
   Switching characteristics are independent of operating junction temperatures.

# **TYPICAL PERFORMANCE CURVES** (T<sub>J</sub> = 25°C unless otherwise noted)



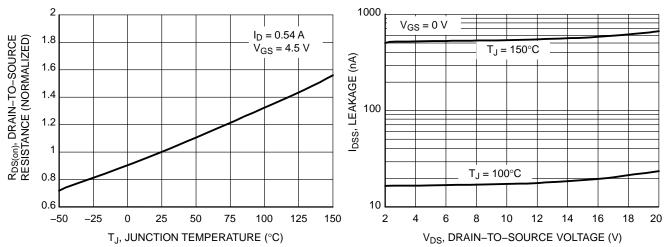
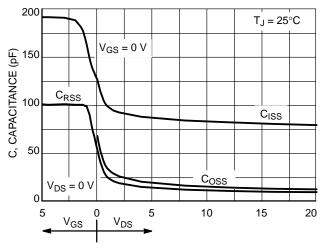


Figure 5. On-Resistance Variation with **Temperature** 

Figure 6. Drain-to-Source Leakage Current versus Voltage

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)

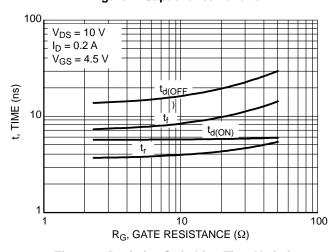


 $^{\rm O}$   $^{\rm R}$   $^{\rm R}$   $^{\rm R}$   $^{\rm S}$   $^{\rm S}$   $^{\rm O}$   $^{\rm SO}$  DRAIN–TO–SOURCE VOLTAGE (V) V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)  $\mathsf{Q}_\mathsf{T}$  $V_{DS}$  $V_{GS}$  $Q_{\mathsf{GD}}$  $Q_{GS}$  $I_D = 0.54 A$  $\overline{T_J} = 25^{\circ}C$ 0 0 0.2 0.4 0.6 8.0 1.2 1.4 1.6 Q<sub>g</sub>, TOTAL GATE CHARGE (nC)

GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (V)

Figure 7. Capacitance Variation

Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge



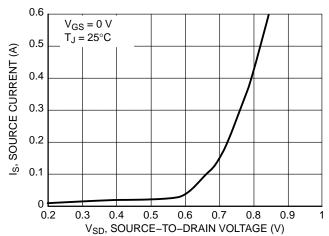


Figure 9. Resistive Switching Time Variation versus Gate Resistance

Figure 10. Diode Forward Voltage versus Current

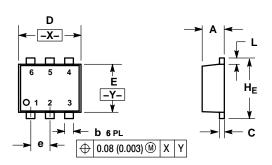
## **ORDERING INFORMATION**

Device	Package	Shipping		
NTZD3154NT1G				
NTZD3154NT1H		4000 / Tana & Basil		
NTZD3154NT2G	SOT-563	4000 / Tape & Reel		
NTZD3154NT2H	(Pb-Free)			
NTZD3154NT5G		0000 / Tana 8 Dagi		
NTZD3154NT5H		8000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

## **SOT-563, 6 LEAD** CASE 463A ISSUE F

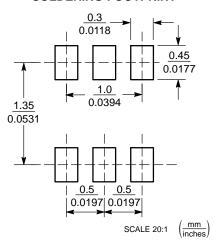


#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
E	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC		(	0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
He	1.50	1.60	1.70	0.059	0.062	0.066	

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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